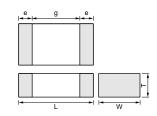
Monolithic Ceramic Capacitors GR_R6/R7/F5/E4 (X5R/X7R/Y5V/Z5U)

High Dielectric Constant Type 6.3/16/25/50V





Part Number		Dimensions (mm)							
Part Number	L	W	T	е	g min.				
GRM155	1.0 ±0.05	0.5 ±0.05	0.5 ±0.05	0.15 to 0.3	0.4				
GRM188*	1.6 ±0.1	0.8 ±0.1	0.8 ±0.1	0.2 to 0.5	0.5				
GRM216			0.6 ±0.1						
GRM219	2.0 ±0.1	1.25 ±0.1	0.85 ±0.1	0.2 to 0.7	0.7				
GRM21B			1.25 ±0.1						
GRM319	2 2 10 15	1.6 ±0.15	0.85 ±0.1						
GRM31M] 3.∠ ±0.15	1.0 ±0.15	1.15 ±0.1	0.3 to 0.8	1.5				
GRM31C	3.2 ±0.2	1.6 ±0.2	1.6 ±0.2						

^{*} Bulk Case : $1.6 \pm 0.07(L) \times 0.8 \pm 0.07(W) \times 0.8 \pm 0.07(T)$

Part Number	TC Code	Rated Voltage (Vdc)	Capacitance*	Length L (mm)	Width W (mm)	Thickness T (mm)
GRM155R61A683KA01	X5R (EIA)	10	68000pF±10%	1.0	0.5	0.50
GRM155R61A104KA01	X5R (EIA)	10	0.1μF±10%	1.0	0.5	0.50
GRM188R61A334KA61	X5R (EIA)	10	0.33 μF±10%	1.6	0.8	0.80
GRM188R61A474KA61	X5R (EIA)	10	0.47μF±10%	1.6	0.8	0.80
GRM188R61A684KA61	X5R (EIA)	10	0.68μF±10%	1.6	0.8	0.80
GRM188R61A105KA61	X5R (EIA)	10	1μF ±10%	1.6	0.8	0.80
GRM188R60J105KA01	X5R (EIA)	6.3	1μF ±10%	1.6	0.8	0.80
GRM219R61A105KC01	X5R (EIA)	10	1μF ±10%	2.0	1.25	0.90
GRM21BR61A225KA01	X5R (EIA)	10	2.2μF ±10%	2.0	1.25	1.25
GRM219R60J155KC01	X5R (EIA)	6.3	1.5μF ±10%	2.0	1.25	0.90
GRM21BR60J225KA01	X5R (EIA)	6.3	2.2μF ±10%	2.0	1.25	1.25
GRM21BR60J335KA11	X5R (EIA)	6.3	3.3μF ±10%	2.0	1.25	1.25
GRM21BR60J475KA11	X5R (EIA)	6.3	4.7μF ±10%	2.0	1.25	1.25
GRM319R61A225KC01	X5R (EIA)	10	2.2μF ±10%	3.2	1.6	0.90
GRM31XR61A335KC12	X5R (EIA)	10	3.3μF ±10%	3.2	1.6	1.30
GRM31CR61A475KA01	X5R (EIA)	10	4.7μF ±10%	3.2	1.6	1.60
GRM31MR60J475KC11	X5R (EIA)	6.3	4.7μF ±10%	3.2	1.6	1.15
GRM31CR61A106KA01	X5R (EIA)	10	10μF ±10%	3.2	1.6	1.60
GRM31CR60J106KA01	X5R (EIA)	6.3	10μF ±10%	3.2	1.6	1.60
GRM31CR60J226ME20	X5R (EIA)	6.3	22μF ±20%	3.2	1.6	1.60
GRM32ER61A106KC01	X5R (EIA)	10	10μF ±10%	3.2	2.5	2.50
GRM55DR61H106KA01	X5R (EIA)	50	10μF ±10%	5.7	5.0	2.00
GRM15XR71H221KA86	X7R (EIA)	50	220pF±10%	1.0	0.5	0.25
GRM155R71H221KA01	X7R (EIA)	50	220pF±10%	1.0	0.5	0.50
GRM15XR71H331KA86	X7R (EIA)	50	330pF±10%	1.0	0.5	0.25
GRM155R71H331KA01	X7R (EIA)	50	330pF±10%	1.0	0.5	0.50
GRM15XR71H471KA86	X7R (EIA)	50	470pF±10%	1.0	0.5	0.25
GRM155R71H471KA01	X7R (EIA)	50	470pF±10%	1.0	0.5	0.50
GRM15XR71H681KA86	X7R (EIA)	50	680pF±10%	1.0	0.5	0.25
GRM155R71H681KA01	X7R (EIA)	50	680pF±10%	1.0	0.5	0.50
GRM15XR71H102KA86	X7R (EIA)	50	1000pF±10%	1.0	0.5	0.25
GRM155R71H102KA01	X7R (EIA)	50	1000pF±10%	1.0	0.5	0.50
GRM15XR71H152KA86	X7R (EIA)	50	1500pF±10%	1.0	0.5	0.25
GRM155R71H152KA01	X7R (EIA)	50	1500pF±10%	1.0	0.5	0.50
GRM155R71H222KA01	X7R (EIA)	50	2200pF±10%	1.0	0.5	0.50



Continued from the preceding page.

Part Number	TC Code	Rated Voltage (Vdc)	Capacitance*	Length L (mm)	Width W (mm)	Thickness T (mm)
GRM155R71H332KA01	X7R (EIA)	50	3300pF±10%	1.0	0.5	0.50
GRM155R71H472KA01	X7R (EIA)	50	4700pF±10%	1.0	0.5	0.50
GRM15XR71E182KA86	X7R (EIA)	25	1800pF±10%	1.0	0.5	0.25
GRM15XR71E222KA86	X7R (EIA)	25	2200pF±10%	1.0	0.5	0.25
GRM155R71E682KA01	X7R (EIA)	25	6800pF±10%	1.0	0.5	0.50
GRM155R71E103KA01	X7R (EIA)	25	10000pF±10%	1.0	0.5	0.50
GRM15XR71C332KA86	X7R (EIA)	16	3300pF±10%	1.0	0.5	0.25
GRM15XR71C472KA86	X7R (EIA)	16	4700pF±10%	1.0	0.5	0.25
GRM15XR71C682KA86	X7R (EIA)	16	6800pF±10%	1.0	0.5	0.25
GRM155R71C153KA01	X7R (EIA)	16	15000pF±10%	1.0	0.5	0.50
GRM155R71C223KA01	X7R (EIA)	16	22000pF±10%	1.0	0.5	0.50
GRM155R71A333KA01	X7R (EIA)	10	33000pF±10%	1.0	0.5	0.50
GRM155R71A473KA01	X7R (EIA)	10	47000pF±10%	1.0	0.5	0.50
GRM188R71H221KA01	X7R (EIA)	50	220pF±10%	1.6	0.8	0.80
GRM188R71H331KA01	X7R (EIA)	50	330pF±10%	1.6	0.8	0.80
GRM188R71H471KA01	X7R (EIA)	50	470pF±10%	1.6	0.8	0.80
GRM188R71H681KA01	X7R (EIA)	50	680pF±10%	1.6	0.8	0.80
GRM188R71H102KA01	X7R (EIA)	50	1000pF±10%	1.6	0.8	0.80
GRM188R71H152KA01	X7R (EIA)	50	1500pF±10%	1.6	0.8	0.80
GRM188R71H222KA01	X7R (EIA)	50	2200pF±10%	1.6	0.8	0.80
GRM188R71H332KA01	X7R (EIA)	50	3300pF±10%	1.6	0.8	0.80
GRM188R71H472KA01	X7R (EIA)	50	4700pF±10%	1.6	0.8	0.80
GRM188R71H682KA01	X7R (EIA)	50	6800pF±10%	1.6	0.8	0.80
GRM188R71H103KA01	X7R (EIA)	50	10000pF±10%	1.6	0.8	0.80
		50	•	1.6	0.8	0.80
GRM188R71H153KA01	X7R (EIA)		15000pF±10%			
GRM188R71H223KA01	X7R (EIA)	50	22000pF±10%	1.6	0.8	0.80
GRM188R71E333KA01	X7R (EIA)	25	33000pF±10%	1.6	0.8	0.80
GRM188R71E473KA01	X7R (EIA)	25	47000pF±10%	1.6	0.8	0.80
GRM188R71E683KA01	X7R (EIA)	25	68000pF±10%	1.6	0.8	0.80
GRM188R71E104KA01	X7R (EIA)	25	0.1μF±10%	1.6	0.8	0.80
GRM188R71C104KA01	X7R (EIA)	16	0.1μF±10%	1.6	0.8	0.80
GRM188R71A154KA01	X7R (EIA)	10	0.15μF±10%	1.6	0.8	0.80
GRM188R71A224KA01	X7R (EIA)	10	22000pF±10%	1.6	0.8	0.80
3RM219R71H333KA01	X7R (EIA)	50	33000pF±10%	2.0	1.25	0.90
GRM21BR71H473KA01	X7R (EIA)	50	47000pF±10%	2.0	1.25	1.25
GRM21BR71H683KA01	X7R (EIA)	50	68000pF±10%	2.0	1.25	1.25
GRM21BR71H104KA01	X7R (EIA)	50	0.1μF±10%	2.0	1.25	1.25
GRM21BR71H154KA01	X7R (EIA)	50	0.15μF±10%	2.0	1.25	1.25
GRM21BR71H224KA01	X7R (EIA)	50	22000pF±10%	2.0	1.25	1.25
GRM21BR71E104KA01	X7R (EIA)	25	0.1μF±10%	2.0	1.25	1.25
GRM21BR71E154KA01	X7R (EIA)	25	0.15μF±10%	2.0	1.25	1.25
GRM219R71E224KC01	X7R (EIA)	25	22000pF±10%	2.0	1.25	0.90
GRM21BR71E334KC01	X7R (EIA)	25	0.33 μF±10%	2.0	1.25	1.25
GRM21BR71E474KC01	X7R (EIA)	25	0.47μF±10%	2.0	1.25	1.25
RM219R71C474KC01	X7R (EIA)	16	0.47μF±10%	2.0	1.25	0.90
RM219R71C684KC01	X7R (EIA)	16	0.68μF±10%	2.0	1.25	0.90
RM21BR71C105KA01	X7R (EIA)	16	1μF ±10%	2.0	1.25	1.25
RM319R71H334KA01	X7R (EIA)	50	0.33 μF±10%	3.2	1.6	0.90
RM31MR71H474KA01	X7R (EIA)	50	0.47μF±10%	3.2	1.6	1.15
RM319R71E684KC01	X7R (EIA)	25	0.68μF±10%	3.2	1.6	0.90
GRM31MR71E105KC01	X7R (EIA)	25	1μF ±10%	3.2	1.6	1.15
GRM319R71C105KC11	X7R (EIA)	16	1μF ±10%	3.2	1.6	0.90
GRM31MR71C155KC11	X7R (EIA)	16	1.5μF ±10%	3.2	1.6	1.15
GRM31MR71C225KA35	X7R (EIA)	16	2.2μF ±10%	3.2	1.6	1.15
- I OZZONAO	X7R (EIA)	10	2.2μι ±10% 1μF ±10%	3.2	1.6	0.90



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Part Number	TC Code	Rated Voltage (Vdc)	Capacitance*	Length L (mm)	Width W (mm)	Thickness (mm)
GRM319R71A225KA01	X7R (EIA)	10	2.2μF ±10%	3.2	1.6	0.90
GRM32NR71H684KA01	X7R (EIA)	50	0.68μF±10%	3.2	2.5	1.35
GRM32RR71H105KA01	X7R (EIA)	50	1μF ±10%	3.2	2.5	1.80
GRM32RR71E225KC01	X7R (EIA)	25	2.2μF ±10%	3.2	2.5	1.80
GRM32MR71C225KC01	X7R (EIA)	16	2.2μF ±10%	3.2	2.5	1.15
GRM32NR71C335KC01	X7R (EIA)	16	3.3μF ±10%	3.2	2.5	1.35
GRM32RR71C475KC01	X7R (EIA)	16	4.7μF ±10%	3.2	2.5	1.80
GRM43ER71H225KA01	X7R (EIA)	50	2.2μF ±10%	4.5	3.2	2.50
GRM55RR71H105KA01	X7R (EIA)	50	1μF ±10%	5.7	5.0	1.80
GRM55RR71H155KA01	X7R (EIA)	50	1.5μF ±10%	5.7	5.0	1.80
GRM155F51H222ZA01	Y5V (EIA)	50	2200pF +80%, -20%	1.0	0.5	0.50
RM155F51H472ZA01	Y5V (EIA)	50	4700pF +80%, -20%	1.0	0.5	0.50
GRM155F51H103ZA01	Y5V (EIA)	50	10000pF +80%, -20%	1.0	0.5	0.50
GRM155F51E223ZA01	Y5V (EIA)	25	22000pF +80%, -20%	1.0	0.5	0.50
GRM155F51C473ZA01	Y5V (EIA)	16	47000pF +80%, -20%	1.0	0.5	0.50
GRM155F51C104ZA01	Y5V (EIA)	16	10000pF +80%, -20%	1.0	0.5	0.50
GRM188F51H103ZA01	Y5V (EIA)	50	10000pF +80%, -20%	1.6	0.8	0.80
GRM188F51H223ZA01	Y5V (EIA)	50	22000pF +80%, -20%	1.6	0.8	0.80
GRM188F51H473ZA01	Y5V (EIA)	50	47000pF +80%, -20%	1.6	0.8	0.80
GRM188F51H104ZA01	Y5V (EIA)	50	10000pF +80%, -20%	1.6	0.8	0.80
GRM188F51E104ZA01	Y5V (EIA)	25	10000pF +80%, -20%	1.6	0.8	0.80
GRM188F51C224ZA01	Y5V (EIA)	16	22000pF +80%, -20%	1.6	0.8	0.80
GRM188F51C474ZA01	Y5V (EIA)	16	0.47μF +80%, -20%	1.6	0.8	0.80
	, ,					
GRM188F51A474ZC01	Y5V (EIA)	10	0.47μF +80%, -20%	1.6	0.8	0.80
GRM188F51A105ZA01	Y5V (EIA)	10	1μF +80%, -20%	1.6	0.8	0.80
GRM219F51H104ZA01	Y5V (EIA)	50	10000pF +80%, -20%	2.0	1.25	0.90
GRM21BF51H224ZA01	Y5V (EIA)	50	22000pF +80%, -20%	2.0	1.25	1.25
GRM219F51E224ZA01	Y5V (EIA)	25	22000pF +80%, -20%	2.0	1.25	0.90
GRM21BF51E474ZA01	Y5V (EIA)	25	0.47μF +80%, -20%	2.0	1.25	1.25
GRM219F51E105ZA01	Y5V (EIA)	25	1μF +80%, -20%	2.0	1.25	0.90
GRM21BF51E225ZA01	Y5V (EIA)	25	2.2μF +80%, -20%	2.0	1.25	1.25
GRM219F51C105ZA01	Y5V (EIA)	16	1μF +80%, -20%	2.0	1.25	0.90
GRM21BF51C225ZA01	Y5V (EIA)	16	2.2μF +80%, -20%	2.0	1.25	1.25
GRM219F51A105ZA01	Y5V (EIA)	10	1μF +80%, -20%	2.0	1.25	0.90
GRM21BF51A225ZA01	Y5V (EIA)	10	2.2μF +80%, -20%	2.0	1.25	1.25
GRM21BF51A475ZA01	Y5V (EIA)	10	4.7μF +80%, -20%	2.0	1.25	1.25
GRM31MF51H474ZA01	Y5V (EIA)	50	0.47μF +80%, -20%	3.2	1.6	1.15
GRM31MF51E105ZA01	Y5V (EIA)	25	1μF +80%, -20%	3.2	1.6	1.15
GRM31MF51E475ZA01	Y5V (EIA)	25	4.7μF +80%, -20%	3.2	1.6	1.15
GRM319F51C105ZA01	Y5V (EIA)	16	1μF +80%, -20%	3.2	1.6	0.90
GRM31MF51C225ZA01	Y5V (EIA)	16	2.2μF +80%, -20%	3.2	1.6	1.15
GRM31MF51C475ZA12	Y5V (EIA)	16	4.7μF +80%, -20%	3.2	1.6	1.15
GRM319F51A225ZA01	Y5V (EIA)	10	2.2μF +80%, -20%	3.2	1.6	0.90
GRM31MF51A475ZA01	Y5V (EIA)	10	4.7μF +80%, -20%	3.2	1.6	1.15
SRM31MF51A106ZA01	Y5V (EIA)	10	10μF +80%, -20%	3.2	1.6	1.15
GRM31MF50J106ZA01	Y5V (EIA)	6.3	10μF +80%, -20%	3.2	1.6	1.15
GRM32RF51H105ZA01	Y5V (EIA)	50	1μF +80%, -20%	3.2	2.5	1.80
GRM329F51E475ZA01	Y5V (EIA)	25	4.7μF +80%, -20%	3.2	2.5	0.90
GRM32NF51E106ZA01	Y5V (EIA)	25	10μF +80%, -20%	3.2	2.5	1.35
GRM32NF51C106ZA01	Y5V (EIA)	16	10μF +80%, -20%	3.2	2.5	1.35
GRM188E41H103MA01	Z5U (EIA)	50	10000pF±20%	1.6	0.8	0.80
GRM188E41H223MA01	Z5U (EIA)	50	22000pF±20%	1.6	0.8	0.80
GRM216E41H473MA01	Z5U (EIA)	50	47000pF±20%	2.0	1.25	0.60
GRM219E41H104MA01	Z5U (EIA)	50	10000pF±20%	2.0	1.25	0.90
GRM319E41H224MA01	Z5U (EIA)	50	22000pF±20%	3.2	1.6	0.70

■ Specifications and Test Methods

		Specifi	cations				
No.	Item	Temperature Compensating Type	High Dielectric Type	Test Method			
1	Operating Temperature Range	–55 to +125℃	B1, B3, F1: -25°C to +85°C R1, R7: -55°C to +125°C E4: +10°C to +85°C F5: -30°C to +85°C	Reference Temperature : 25° C (2Δ , 3Δ , 4Δ , B1, B3, F1, R1 : 20° C)			
2	Rated Voltage	See the previous pages		The rated voltage is defined as the maximum voltage which may be applied continuously to the capacitor. When AC voltage is superimposed on DC voltage, V ^{p,p} or V ^{o,p} , whichever is larger, should be maintained within the rated voltage range.			
3	Appearance	No defects or abnormalities		Visual inspection			
4	Dimensions	Within the specified dimensions	1	Using calipers			
5	Dielectric Strength	No defects or abnormalities		No failure should be observed when 300% of the rated voltage (temperature compensating type) or 250% of the rated voltage (high dielectric constant type) is applied between the terminations for 1 to 5 seconds, provided the charge/discharge current is less than 50mA.			
6	Insulation Resistance	C≦0.047μF : More than 10,0000 C>0.047μF : 500Ω • F	MΩ C : Nominal Capacitance	The insulation resistance should be measured with a DC voltage not exceeding the rated voltage at 20°C/25°C and 75%RH max. and within 2 minutes of charging, provided the charge/discharge current is less than 50mA.			
7	Capacitance	Within the specified tolerance		The capacitance/D.F. should be measured at 20℃/25℃ at the			
8	Q/ Dissipation Factor (D.F.)	30pF and over : Q≥1000 30pF and below : Q≥400+20C C : Nominal Capacitance (pF)	[B1, B3, R1, R6, R7, E4] W.V.: 25Vmin.: 0.025max. W.V.: 16/10V: 0.035max. W.V.: 6.3V/4V : 0.05max. (C<3.3μF) : 0.1max. (C≧3.3μF) [F1, F5] W.V.: 25Vmin. : 0.05max. (C<0.1μF) : 0.09max. (C≥0.1μF) W.V.: 16V/10V: 0.125max. W.V.: 6.3V: 0.15max.				



Ontinued from the preceding page.

			Specifi	cations					
No.	Ite	em	Temperature Compensating Type	High Dielectric Type			Test Me	thod	
		No bias	Within the specified tolerance (Table A-1)	B1, B3 : Within±10% (-25°C to +85°C) R1, R7 : Within±15% (-55°C to +125°C) R6 : Within±15% (-55°C to +85°C) E4 : Within +22/-56% (+10°C to +85°C) F1 : Within +30/-80% (-25°C to +85°C) F5 : Within +22/-82% (-30°C to +85°C)	each speci (1)Tempers The tempers measured When cyclic 5 (5C: +29 coeffs: +2 should be coefficient The capaci between the	fied temperature Corrature coin step 3 ng the tescent to +125°C to +within the and capa itance drive maxim	o. stage. mpensating Ty efficient is determined as a reference mperature security 85°C/AC: +20 85°C/+20°C to e specified tole incitance chang ft is caluculate um and minim	rpe ermind u e. quentially ℃ to +12 +85℃) the rance for ge as Tab ed by divi	ding the differences sured values in the
					step 1, 3 a		ne cap. value i	n step 3. emperatu	
		50% of the Rated		B1 : Within +10/-30% R1 : Within +15/-40%		•		•	perature±2
		Voltage		F1 : Within +30/–95%		2			±3 (for other TC)
						3	Refere	nce Tem	perature±2
						1	125±3 (for	∆C)/85±	3 (for other TC)
						5	Refere	nce Tem	perature±2
9	Capacitance Temperature Characteristics				The ranges value over be within the ln case of a measured	s of capa- the temp ne specifi applying after 1 m	erature ranges ed ranges.*	s shown	red with the 20°C in the table should se change should be voltage in
					Step		nperature (°C)		Applying Voltage (V)
		Capacitance Drift	Within ±0.2% or ±0.05pF (Whichever is larger.) *Not apply to 1X/25V	*Initial measurement for high dielectric constant type Perform a heat treatment at 150+0/-10°C for one hour	1 2 3 4	Refere -55± -25± -30±3 (Refere	nce Temperet :3 (for R1, R7, :3 (for B1, B3, (for F5)/10±3 (nce Temperet 5±3 (for R1, R :3 (for B1, B3, F1, F5, E4)	R6) F1) (for E4) ure±2 7)/	No bias
				and then set for 48±4 hours at room temperature.	5	Refere	nce Temperet	ure±2	_
				Perform the initial measurement.	6		55±3 (for R1), 5±3 (for B1, F		50% of the rated
					7		nce Temperet		voltage
					8		25±3 (for R1), 5±3 (for B1, F1		
			No removal of the terminations	or other defect should occur	Fig. 1a using parallel with The solder reflow method soldering is	ng an eut h the test ing shoul nod and s s uniform	ectic solder. T i jig for 10±1 s d be done eith should be cond	hen applec. Her with a ducted we fects such	poxy board) shown in ly 10N* force in in iron or using the ith care so that the ch as heat shock.
	Adhosivo	Strength							(in mm)
10	of Termin				Ty		a 0.3	b	C 0.3
					_GR□03 GR□15		0.3	0.9 1.5	0.3
				Solder resist	GRM18		1.0	3.0	1.2
				Baked electrode or	GRM21		1.2	4.0	1.65
				copper foil	GRM31		2.2	5.0	2.0
			Fig. 1a		GRM32		2.2	5.0	2.9
					GRM43 GRM55		3.5 4.5	7.0 8.0	3.7 5.6
					GRIVIOS	,	+.∪	0.0	5.0
							Со	ntinued or	n the following page.

Continued from the preceding page.

		om the prec		cations				
No.	lte	em	Temperature Compensating Type	High Dielectric Type	-	Test Me	thod	
		Appearance Capacitance	No defects or abnormalities Within the specified tolerance	[B1, B3, R1, R6, R7, E4]	Solder the capa	citor on the test jig	ı (glass epo	xy board) in the
11	Vibration Resistance	Q/D.F.	30pF and over : Q≥1000 30pF and below : Q≥400+20C C : Nominal Capacitance (pF)	W.V.: 25Vmin.: 0.025max. W.V.: 16/10V: 0.035max. W.V.: 6.3V/4V : 0.05max. (C<3.3μF) : 0.1max. (C≥3.3μF) [F1, F5] W.V.: 25Vmin. : 0.05max. (C<0.1μF) : 0.09max. (C≥0.1μF) W.V.: 16V/10V: 0.125max. W.V.: 6.3V: 0.15max.	same manner and under the same conditions as (10). The capacitor should be subjected to a simple harmonic n having a total amplitude of 1.5mm, the frequency being va uniformly between the approximate limits of 10 and 55Hz. frequency range, from 10 to 55Hz and return to 10Hz, sho be traversed in approximately 1 minute. This motion shoul applied for a period of 2 hours in each 3 mutually perpend directions (total of 6 hours).			
			No crack or marked defect should occur		Solder the capacitor on the test jig (glass epoxy board) shown in Fig. 2a using an eutectic solder. Then apply a force in the direction shown in Fig. 3a for 5±1sec. The soldering should be done either with an iron or using the reflow method and should be conducted with care so that the soldering is uniform and free			y a force in the oldering should be ethod and should
12	Defle	ction	R230 Capacitance in	Pressurizing speed : 1.0mm/sec. Pressurize Flexure : ≦1	Type GR□03 GR□15 GRM18 GRM21 GRM31 GRM32 GRM43 GRM55	a 0.3 0.4 1.0 1.2 2.2 2.2 3.5 4.5		□03/15:t:0.8mm)
13	Solderab Terminati		75% of the terminations are to be continuously The measured and observed ch	ŕ	rosin (JIS-K-590 Preheat at 80 to	02) (25% rosin in w 0 120°C for 10 to 30 1, immerse in an e	veight propo) seconds.	
			specifications in the following ta	-				
		Appearance	No defects or abnormalities					
		Capacitance Change	Within ±2.5% or ±0.25pF (Whichever is larger)	B1, B3, R1, R6, R7 : Within ±7.5% F1, F5, E4 : Within ±20%	Immerse the ca	acitor at 120 to 15 pacitor in an euted ands. Set at room t	tic solder so	olution at 270±5℃
14	Resistance to Soldering Heat	30pF and over : Q≧1000 dering Q/D.F. 30pF and below :		[B1, B3, R1, R6, R7, E4] W.V.: 25Vmin.: 0.025max. W.V.: 16/10V: 0.035max. W.V.: 6.3V/4V : 0.05max. (C<3.3µF) : 0.1max. (C≥3.3µF) [F1, F5] W.V.: 25Vmin. : 0.05max. (C<0.1µF) : 0.09max. (C≥0.1µF) W.V.: 16V/10V: 0.125max. W.V.: 6.3V: 0.15max.	(temperature compensating tyoe) or 48±4 hours (high dielectonstant type), then measure. •Initial measurement for high dielectric constant type Perform a heat treatment at 150+0/−10℃ for one hour and then set at room temperature for 48±4 hours. Perform the initial measurement. •Preheating for GRM32/43/55 Step Temperature Time 1 100℃ to 120℃ 1 min.			urs (high dielectric ant type one hour and
		I.R.	More than $10,000 \mathrm{M}\Omega$ or 500Ω	F (Whichever is smaller)				
		Dielectric Strength	No defects					

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		Specifi	cations							
No. It	em	Temperature Compensating Type	High Dielectric Type		Tes	t Method	i			
		The measured and observed ch specifications in the following ta	-							
	Appearance	No defects or abnormalities		1						
	Capacitance Change	Within ±2.5% or ±0.25pF (Whichever is larger)	B1, B3, R1, R6, R7 : Within ±7.5% F1, F5, E4 : Within ±20%	Fix the capacitor to the supporting jig in the sar manner and under the same conditions as (10) Perform the five cycles according to the four he shown in the following table.		s as (10).	atments			
			[B1, B3, R1, R6, R7, E4] W.V.: 25Vmin.: 0.025max. W.V.: 16/10V: 0.035max.	Set for 24±2 he hours (high die measure.	ours (temperat		t room tempera			
15 Temperature		30pF and over : Q≥1000 30pF and below : .F. Q≥400+20C	W.V.: 6.3V/4V	Step	1	2	3	4		
Cycle	Q/D.F.		: 0.05max. (C<3.3µF) : 0.1max. (C≧3.3µF) [F1, F5]	Temp. (℃)	Min. Operating Temp.+0/-3	Room Temp.	Max. Operating Temp.+3/-0	Room Temp.		
		C : Nominal Capacitance (pF)	W.V. : 25Vmin.	Time (min.)	30±3	2 to 3	30±3	2 to 3		
D			: 0.05max. (C<0.1µF) : 0.09max. (C≥0.1µF) W.V. : 16V/10V : 0.125max. W.V. : 6.3V : 0.15max.	•Initial measurement for high dielectric constant type Perform a heat treatment at 150+0/-10°C for one hour and then set at room temperature for 48±4 hours. Perform the initial measurement.						
	I.R.	More than $10,000 \mathrm{M}\Omega$ or 500Ω								
	Dielectric Strength	No defects								
			he measured and observed characteristics should satisfy the pecifications in the following table							
	Appearance	No defects or abnormalities								
	Capacitance Change	Within ±5% or ±0.5pF (Whichever is larger)	B1, B3, R1, R6, R7, C8 : Within ±12.5% F1, F5 : Within ±30%							
Humidity 16 (Steady State)	30pF and over : Q≥350 10pF and over 30pF and below : Q≥275+2.5C		[B1, B3, R1, R6, R7, E4] W.V.: 25Vmin.: 0.05max. W.V.: 16/10V: 0.05max. W.V.: 6.3V/4V : 0.075max. (C<3.3µF) : 0.125max. (C≥3.3µF)	Set the capacitor at 40±2°C and in 90 to 95% humiduty for 500±12 hours. Remove and set for 24±2 hours (temperature compensatin type) or 48±4 hours (high dielectric constant type) at room temperature, then measure.			ensating			
	Q/D.F.	10pF and below : Q≥200+10C C : Nominal Capacitance (pF)	[F1, F5] W.V.: 25Vmin. : 0.075max. (C<0.1μF) : 0.125max. (C≥0.1μF) W.V.: 16V/10V: 0.15max. W.V.: 6.3V: 0.2max.							
	I.R.	More than $1,000M\Omega$ or $50\Omega \bullet F$	1							

Continued on the following page. $\begin{tabular}{|c|c|c|c|}\hline \end{tabular}$

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		Specifi	ications	
No.	Item	Temperature Compensating Type	High Dielectric Type	Test Method
		The measured and observed chapecifications in the following ta	-	
	Appearance	No defects or abnormalities		
	Capacitance Change	Within ±7.5% or ±0.75pF (Whichever is larger)	B1, B3, R1, R6, R7 : Within ±12.5% F1, F5, E4: Within ±30% [W.V.: 10Vmax.] F1, F5: Within +30/-40%	Apply the rated voltage at 40±2°C and 90 to 95% humidity for 500±12 hours. Remove and set for 24±2 hours (temperature
17 Humidi Load	Q/D.F.	30pF and over : Q≥200 30pF and below : Q≥100+10C/3 C : Nominal Capacitance (pF)	[B1, B3, R1, R6, R7, E4] W.V.: 25Vmin.: 0.05max. W.V.: 16/10V: 0.05max. W.V.: 6.3V : 0.075max. (C<3.3μF) : 0.125max. (C≧3.3μF) [F1, F5] W.V.: 25Vmin. : 0.075max. (C<0.1μF) : 0.125max. (C≥0.1μF) W.V.: 16V/10V: 0.15max. W.V.: 6.3V: 0.2max.	 compensating type) or 48±4 hours (high dielectric constant type) at room temprature, then muasure. The charge/discharge current is less than 50mA. Initial measurement for F1, F5/10V max. Apply the rated DC voltage for 1 hour at 40±2°C. Remove and set for 48±4 hours at room temperature. Perform initial measurement.
	I.R.	More than 500MΩ or 25Ω • F (\	Vhichever is smaller)	
		The measured and observed chapecifications in the following ta	-	
	Appearance	No defects or abnormalities		
	Capacitance Change	Within ±3% or ±0.3pF (Whichever is larger)	B1, B3, R1, R6, R7 : Within ±12.5% F1, F5, E4: Within ±30% [Exept 10Vmax. and. C≥1.0µF] F1, F5: Within +30/-40% [10Vmax. and. C≥1.0µF]	Apply 200% of the rated voltage at the maximum operating temperature ±3°c for 1000±12 hours. Set for 24±2 hours (temperature compensating type) or 48±4 hours (high dielectric constant type) at room temperature, then measure.
High 18 Temperatu Load	Q/D.F.	30pF and over : Q≥350 10pF and over 30pF and below : Q≥275+2.5C 10pF and below : Q≥200+10C C : Nominal Capacitance (pF)	[B1, B3, R1, R6, R7, E4] W.V.: 25Vmin.: 0.04max. W.V.: 16/10V: 0.05max. W.V.: 6.3V : 0.075max.(C≤3.3μF) : 0.125max.(C≥3.3μF) [F1, F6] W.V.: 25Vmin. : 0.075max.(C<0.1μF) : 0.125max.(C≥0.1μF) W.V.: 16V/10V: 0.15max. W.V.: 6.3V: 0.2max.	The charge/discharge current is less than 50mA. •Initial measurement for high dielectric constant type. Apply 200% of the rated DC voltage at the maximun operating temperature ±3°C for one hour. Remove and set for 48±4 hours at room temperature. Perform initial measurement.
	I.R.	More than 1,000M Ω or 50 Ω •F (Whichever is smaller)	

Continued from the preceding page.

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Table A-1

(1)

		Capacitance Change from 25℃ (%)						
Char.	Nominal Values (ppm/°C)*1	-55		_	-30		-10	
		Max.	Min.	Max.	Min.	Max.	Min.	
5C	0± 30	0.58	-0.24	0.40	-0.17	0.25	-0.11	
6C	0± 60	0.87	-0.48	0.59	-0.33	0.38	-0.21	
6P	-150± 60	2.33	0.72	1.61	0.50	1.02	0.32	
6R	-220± 60	3.02	1.28	2.08	0.88	1.32	0.56	
6S	-330± 60	4.09	2.16	2.81	1.49	1.79	0.95	
6T	-470± 60	5.46	3.28	3.75	2.26	2.39	1.44	
7U	-750±120	8.78	5.04	6.04	3.47	3.84	2.21	
1X	+350 to -1000	_	_	_	_	_	_	

^{*1}Nominal values denote the temperature coefficient within a range of 25°C to 125°C (for Δ C)/85°C (for other TC).

(2)

(2)							
	Capacitance Change from 20℃ (%)						
Char.	Nominal Values (ppm/℃)*2	-	-55	_	-25	_	10
	-	Max.	Min.	Max.	Min.	Max.	Min.
2C	0± 60	0.82	-0.45	0.49	-0.27	0.33	-0.18
3C	0±120	1.37	-0.90	0.82	-0.54	0.55	-0.36
4C	0±250	2.56	-1.88	1.54	-1.13	1.02	-0.75
2P	-150 ± 60	_	_	1.32	0.41	0.88	0.27
3P	-150±120	_	_	1.65	0.14	1.10	0.09
4P	-150±250	_	_	2.36	-0.45	1.57	-0.30
2R	-220 ± 60	_	_	1.70	0.72	1.13	0.48
3R	-220±120	_	_	2.03	0.45	1.35	0.30
4R	-220±250	_	_	2.74	-0.14	1.83	-0.09
2S	-330 ± 60	_	_	2.30	1.22	1.54	0.81
3S	-330±120	_	_	2.63	0.95	1.76	0.63
4S	-330±250	_	_	3.35	0.36	2.23	0.24
2T	-470 ± 60	_	_	3.07	1.85	2.05	1.23
3T	-470±120	_	_	3.40	1.58	2.27	1.05
4T	-470±250	_	-	4.12	0.99	2.74	0.66
3U	-750±120	_	_	4.94	2.84	3.29	1.89
4U	-750±250	_	_	5.65	2.25	3.77	1.50

^{*2}Nominal values denote the temperature coefficient within a range of 20°C to 125°C (for Δ C)/85°C (for other TC).

Monolithic Ceramic Capacitors GR_R6/R7/F5/E4 (X5R/X7R/Y5V/Z5U)

High Dielectric Constant Type 100V

Part Number	TC Code	Rated Voltage (Vdc)	Capacitance*	Length L (mm)	Width W (mm)	Thickness T (mm)
GRM188R72A222KD01	X7R (EIA)	100	2200pF±10%	1.6	0.8	0.80
GRM188R72A332KD01	X7R (EIA)	100	3300pF±10%	1.6	0.8	0.80
GRM219R72A472KA01	X7R (EIA)	100	4700pF±10%	2.0	1.25	0.90
GRM219R72A682KA01	X7R (EIA)	100	6800pF±10%	2.0	1.25	0.90
GRM21BR72A103KA01	X7R (EIA)	100	10000pF±10%	2.0	1.25	1.25
GRM31MR72A333KA01	X7R (EIA)	100	33000pF±10%	3.2	1.6	1.15
GRM31MR72A473KA01	X7R (EIA)	100	47000pF±10%	3.2	1.6	1.15
GRM32NR72A683KA01	X7R (EIA)	100	68000pF±10%	3.2	2.5	1.35
GRM32NR72A104KA01	X7R (EIA)	100	0.1μF±10%	3.2	2.5	1.35
GRM43RR72A154KA01	X7R (EIA)	100	0.15μF±10%	4.5	3.2	1.80
GRM43RR72A224KA01	X7R (EIA)	100	22000pF±10%	4.5	3.2	1.80
GRM43DR72A474KA01	X7R (EIA)	100	0.47μF±10%	4.5	3.2	2.00
GRM55DR72A105KA01	X7R (EIA)	100	1μF ±10%	5.7	5.0	2.00
GRM188F52A472ZD01	Y5V (EIA)	100	4700pF +80%, -20%	1.6	0.8	0.80
GRM32NF52A104ZA01	Y5V (EIA)	100	10000pF +80%, -20%	3.2	2.5	1.35
GRM55RF52A474ZA01	Y5V (EIA)	100	0.47μF +80%, -20%	5.7	5.0	1.80

Monolithic Ceramic Capacitors GR_R6/R7/F5/E4 (X5R/X7R/Y5V/Z5U)

Thin Layer Large-Capacitance type

Part Number		Dime	nsions (mi	m)		
Part Number	L	W	T	e min.	g min.	-
GRM033	0.6 ±0.03	0.3 ±0.03	0.3 ±0.03	0.1 to 0.2	0.2	S
GRM155	1.0 ±0.05	0.5 ±0.05	0.5 ±0.05	0.15 to 0.3	0.4	2 2 2 2
GRM185	1.6 ±0.1	0.8 ±0.1	0.5 +0/-0.2	0.2 to 0.5	0.5	20202
GRM188	1.6 ±0.1	0.8 ±0.1	0.8 ±0.1	0.2 to 0.5	0.5	
GRM216			0.6 ±0.1			
GRM219	2.0 ±0.1	1.25 ±0.1	0.85 ±0.1	0.2 to 0.7	0.7	
GRM21B			1.25 ±0.1			
GRM316			0.6 ±0.1			
GRM319	3.2 ±0.15	1.6 ±0.15	0.85 ±0.1	0.3 to 0.8	1.5	e g e
GRM31M			1.15 ±0.1	0.3 10 0.6	1.3	
GRM31C	3.2 ±0.2	1.6 ±0.2	1.6 ±0.2			
GRM32D	3.2 ±0.3	2.5 ±0.2	2.0 ±0.2	0.3	1.0	
GRM32E	3.2 ±0.3	2.5 ±0.2	2.5 ±0.2	0.3	1.0	
GRM43D			2.0 ±0.2			T T
GRM43E	4.5 ±0.4	3.2 ±0.3	2.5 ±0.2	0.3	2.0	<u> </u>
GRM43S			2.8 ±0.2			L W
GRM55F	5.7 ±0.4	5.0 ±0.4	3.2 ±0.2	0.3	2.0	

Part Number	TC Code	Rated Voltage (Vdc)	Capacitance*	Length L (mm)	Width W (mm)	Thickness T (mm)
GRM155R60J154KE01	X5R (EIA)	6.3	0.15μF±10%	1.0	0.5	0.50
GRM155R60J224KE01	X5R (EIA)	6.3	22000pF±10%	1.0	0.5	0.50
GRM155R60J334KE01	X5R (EIA)	6.3	0.33 μF±10%	1.0	0.5	0.50
GRM155R60J474KE19	X5R (EIA)	6.3	0.47μF±10%	1.0	0.5	0.50
GRM188R60J225KE01	X5R (EIA)	6.3	2.2μF ±10%	1.6	0.8	0.80
GRM219R60J475KE01	X5R (EIA)	6.3	4.7μF ±10%	2.0	1.25	0.90
GRM21BR60J106KE01	X5R (EIA)	6.3	10μF ±10%	2.0	1.25	1.25
GRM21BR60J106ME01	X5R (EIA)	6.3	10μF ±20%	2.0	1.25	1.25
GRM32DR60J226KA01	X5R (EIA)	6.3	22μF ±10%	3.2	2.5	2.00
GRM32ER60J476ME20	X5R (EIA)	6.3	47μF ±20%	3.2	2.5	2.50
GRM43SR60J107ME20	X5R (EIA)	6.3	100μF ±20%	4.5	3.2	2.80
GRM55FR60J107KA01	X5R (EIA)	6.3	100μF ±10%	5.7	5.0	3.20
GRM55FR60J107MA01	X5R (EIA)	6.3	100μF ±20%	5.7	5.0	3.20
GRM21BF50J106ZE01	Y5V (EIA)	6.3	10μF +80%, -20%	2.0	1.25	1.25

No.	Ite	em	Specifications		Test Method	
1	Operating Tempera Range	-	B1, B3, F1: -25°C to +85°C R6: -55°C to +85°C F5: -30°C to +85°C C8: -55°C to +105°C, C7: -55°C to +125°C	Reference (B1, B3, F	Temperature : 25℃ 1 : 20℃)	
2	Rated Vo	ltage	See the previous pages	may be ap When AC	voltage is defined as the maximplied continuously to the capac voltage is superimposed on DC is larger, should be maintained age.	itor. Voltage, V ^{p.p} or V ^{o.p} ,
3	Appearar	nce	No defects or abnormalities	Visual insp	ection	
4	Dimensio	ins	Within the specified dimensions	Using calip	ers	
5		Strength	No defects or abnormalities	No failure s	should be observed when 2509 between the terminations for 1 he charge/discharge current is I	to 5 seconds,
6	Insulation Resistant		More than 50Ω • F	not exceed 75%RH ma	ion resistance should be measu ing the rated voltage at Referer ax. and within 1 minutes of chan charge current is less than 50m.	nce Temperature and ging, provided the
			Within the specified tolerance	•	itance should be measured at I ire at the frequency and voltage	
			*Table 1		apacitance Frequency	
7	Canacita	nco	GRM155 B3/R6 1A 124 to 224	C≦10 C≤10	μF (10V min.)*1 1±0.1kHz μF (6.3V max.) 1±0.1kHz	1.0±0.2Vrms
,	Capacita	lice	GRM185 B3/R6 1A 105	<u>C≦10</u> C>10		0.5±0.1Vrms 0.5±0.1Vrms
			GRM188 B3/R6 1C/1A 225		12022112	0.020.171110
			GRM219 B3/R6 1A 475 GRM21B B3/R6 1C/1A 106		wever the Voltage is $0.5 \pm /-0.1$ ns on the left side.	Vrms about Table 1
			B1, B3, R6, C7, C8 : 0.1 max. F1, F5 : 0.2 max.		hould be measured at Reference and voltage shown in the table	·
			*Table 1		apacitance Frequency	
0	Dissipation	on Factor	GRM155 B3/R6 1A 124 to 224		μF (10V min.)*1 1±0.1kHz	1.0±0.2Vrms
8	(D.F.)		GRM185 B3/R6 1A 105	<u>C≦10</u> C>10	μF (6.3V max.) 1±0.1kHz μF 120±24Hz	0.5±0.1Vrms 0.5±0.1Vrms
			GRM188 B3/R6 1C/1A 225	02 10	μι 120±24112	0.5±0.171113
			GRM219 B3/R6 1A 475 GRM21B B3/R6 1C/1A 106		wever the Voltage is $0.5 \pm /-0.1$ ns on the left side.	Vrms about Table 1
		No bias	B1, B3 : Within +/-10% (-25°C to +85°C) F1 : Within +30/-80% (-25°C to +85°C) R6 : Within +/-15% (-55°C to +85°C) F5 : Within +22/-82% (-30°C to +85°C) C7 : Within +/-22% (-55°C to +125°C) C8 : Within +/-22% (-55°C to +105°C)	each speci The ranges Reference shown in the In case of a measured	itance change should be meas fied temp. stage. s of capacitance change comparements of capacitance change comparements over the tene table should be within the spapplying voltage, the capacitan after 1 more min. with applying n of each temp. stage.	ared with the mperature ranges pecified ranges.* ce change should be
				*GRM43 F	31/R6 0J/1A 336/476 only : 1.0	+0.2Vrms
				Step	Temperature (°C)	Applying Voltage (V)
				1	Reference Tempereture±2	Traphymig remage (r)
9	Capacitance Temperature			2	-55±3 (for R6, C7, C8)/ -25±3 (for B1, B3, F1) -30±3 (for F5)	
	Characteristics			3	Reference Tempereture±2	No bias
		50% of	B1: Within +10/-30%	4	85±3 (for B1, B3, F1, R6, F5) 125±3 (for C7)/ 105±3 (for C8)/	
		the Rated	F1: Within +30/-95%		20±2	
		Voltage				F00/ cf.th
				6	-25±3 (for B1, F1)	50% of the rated
				7	20±2	voltage
				8	85±3 (for B1, F1)	
				Perform a then set fo	asurement for high dielectric co heat treatment at 150 +0/-10° r 48±4 hours at room temperat e initial measurement.	C for one hour and



No.	Item	Specifications		Test Me	ethod			
		No removal of the terminations or other defects should occu		Solder the capacitor on the test jig (glass epoxy board) shown in Fig. 1a using an eutectic solder. Then apply 10N* force in parallel with the test jig for 10+/-1sec. The soldering should be done either with an iron or using the reflow method and should be conducted with care so that the soldering is uniform and free of defects such as heat shock. *5N: GR□15/GRM18, 2N: GR□33				
10	Adhesive Strength of Termination	Solder resist	Type GR□03 GR□15 GRM18	a 0.3 0.4 1.0	b 0.9 1.5 3.0	0.3 0.5 1.2		
		Baked electrode or copper foil	GRM21 GRM31 GRM32	1.2 2.2 2.2	4.0 5.0 5.0	1.65 2.0 2.9		
		Fig. 1a	GRM43 GRM55	3.5 4.5	7.0 8.0	3.7 5.6		
	Appearance	No defects or abnormalities	Solder the capacito	or on the test ii	a (alass epoxy	board) in the		
11	Capacitance Vibration D.F.	Within the specified tolerance B1, B3, R6, C7, C8 : 0.1 max. F1, F5 : 0.2 max.	same manner and The capacitor shot having a total amp uniformly between frequency range, fi be traversed in api applied for a perior directions (total of	under the samuld be subjected litude of 1.5mm the approximator 10 to 55Hz proximately 1 rd of 2 hours in	ne conditions a ed to a simple h n, the frequence ate limits of 10 z and return to minute. This m	s (10). narmonic motion by being varied and 55Hz. The 10Hz, should otion should be		
		No cracking or marking defects should occur 20 50 Pressunzing speed: 1.0mm/sec. Pressunze R230 Flexure: ≤1	Solder the capacitrin Fig. 2a using an direction shown in be done either with should be conduct and free of defects	eutectic solde Fig. 3a for 5+/ n an iron or usi ed with care so	r. Then apply a /—1 sec. The s ng the reflow rother than the solder	a force in the oldering should nethod and		
12	Deflection	Capacitance meter	100 t:1.6mm					
		 -			(GR□03, GR	:□15 : t : 0.8mm)		
		Fig.3a	Type	0.3	0.9	0.3		
		g		0.3	1.5	0.5		
			GRM18	1.0	3.0	1.2		
			GRM21	1.2	4.0	1.65		
			GRM31	2.2	5.0	2.0		
			GRM32	2.2	5.0	2.9		
			GRM43	3.5	7.0	3.7		
			GRM55	4.5	8.0	5.6 (in mm)		
13	Solderability of Termination	75% of the terminations is to be soldered evenly and continuously	Immerse the capar rosin (JIS-K-5902) Preheat at 80 to 12 After preheating, ir 2+/-0.5 seconds	(25% rosin in 20℃ for 10 to 3 mmerse in an e	weight propotions weight propotions weight proposed with the seconds.	on) .		

 $\begin{tabular}{|c|c|c|c|}\hline \end{tabular}$ Continued from the preceding page.

lo. Ite	em	Specifications	Test Method						
Resistance to Soldering Heat	Appearance Capacitance Change Q/D.F. I.R. Dielectric Strength	No defects or abnormalities B1, B3, R6, C7, C8 : Within ±7.5% F1, F5 : Within ±20% B1, B3, R6, C7, C8 : 0.1 max. F1, F5 : 0.2 max. More than 50Ω • F No defects	Preheat the capacitor at 120 to 150°C for 1 minute. Immerse the capacitor in an eutectic solder solution at 270+/-5°C for 10+/-0.5 seconds. Set at room temperature for 24+/-2 hours (temperature compensating tyoe) or 48+/-4 hours (high dielectric constant type), then measure. •Initial measurement for high dielectric constant type Perform a heat treatment at 150+0/-10°C for one hour and then set at room temperature for 48+/-4 hours. Perform the initial measurement.						
			*Preheating fo			Т:	im a		
			Step 1	•	erature		min.		
			2						
	Appearance Capacitance Change D.F.	No defects or abnormalities B1, B3, R6, C7, C8 : Within ±7.5% F1, F5 : Within ±20% B1, B3, R6, C7, C8 : 0.1 max. F1, F5 : 0.2 max. More than 50Ω • F	2 170°C to 200°C 1 min. Fix the capacitor to the supporting jig in the same manner are under the same conditions as (10). Perform the five cycles according to the four heat treatments shown in the following table. Set for 24+/−2 hours (temperature compensating type) or 48+/−4 hours (high dielectric constant type) at room temperature, then measure.						
Temperature	Dielectric	No defects	Step	1	2	3	4		
5 Sudden Change	Strength	No delects	Temp. (°C)	Min. Operating Temp. +0/-3 30±3	Room Temp.	Max. Operating Temp. +3/-0 30±3	Room Temp.		
High Temperature	Appearance Capacitance Change D.F.	No defects or abnormalities B1, B3, R6, C7, C8: Within ±12.5% F1, F5: Within ±30% B1, B3, R6, C7, C8: 0.2 max. F1, F5: 0.4 max.	 Initial measurement for high dielectric constant type Perform a heat treatment at 150+0/-10°C for one hour and then set at room temperature for 48+/-4 hours. Perform the initial measurement. Apply the rated voltage at 40+/-2°C and 90 to 95% humidity 500+/-12 hours. The charge/discharge currentis less than 50mA. Initial measurement 						
High Humidity (Steady)	I.R.	More than 12.5Ω • F	then let sit for initial measure •Measuremen Perform a hea	Perform a heat treatment at 150+0/−10°C for one hour and then let sit for 48+/−4 hours at room temperature. Perform initial measurement. •Measurement after test Perform a heat treatment at 150+0/−10°C for one hour and then let sit for 48+/−4 hours at room temperature, then measure.					
	Appearance	No defects or abnormalities			-	000+/-12 hour			
	Capacitance Change	B1, B3, R6, C7, C8 : Within ±12.5% F1, F5 : Within ±30%	hours at room	rating tempera temperature, t ischarge currei	hen mea		+0⊤/−4		
	D.F.	B1, B3, R6, C7, C8 : 0.1 max. F1, F5 : 0.4 max.		•Initial measurement Perform a heat treatment at 150+0/−10°C for one hour a			or -l		
7 Durability	I.R.	More than 25Ω • F		48+/-4 hours		temperature. P			
				it treatment at		-10℃ for one ho temperature, th			